

Title (en)
OPTOELECTRONIC SEMICONDUCTOR CHIP

Title (de)
OPTOELEKTRONISCHER HALBLEITERCHIP

Title (fr)
PUCE À SEMI-CONDUCTEUR OPTOÉLECTRONIQUE

Publication
EP 2319097 A1 20110511 (DE)

Application
EP 09776012 A 20090723

Priority
• DE 2009001038 W 20090723
• DE 102008045028 A 20080829

Abstract (en)
[origin: WO2010022694A1] A semiconductor chip is specified, comprising an active layer (2) provided for emitting an electromagnetic radiation, and a two-dimensional arrangement of structure units (5), which is disposed downstream of the active layer in a main emission direction (6) of the semiconductor chip. The structure units (5) are arranged in an arbitrary statistical distribution. A semiconductor chip having a directional emission characteristic can be realized by means of such an arrangement of structure units.

IPC 8 full level
H01L 33/00 (2010.01)

CPC (source: EP KR US)
H01L 33/10 (2013.01 - KR); **H01L 33/22** (2013.01 - EP KR US); **H01L 33/405** (2013.01 - EP US); **H01L 33/46** (2013.01 - EP US)

Citation (search report)
See references of WO 2010022694A1

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DE 102008045028 A1 20100304; **DE 102008045028 B4 20230316**; CN 102138229 A 20110727; CN 102138229 B 20151125; EP 2319097 A1 20110511; KR 20110056386 A 20110527; TW 201023406 A 20100616; TW I427826 B 20140221; US 2011297982 A1 20111208; WO 2010022694 A1 20100304

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